



FEATURES

- 1.8 Ω maximum on resistance at 25°C
- 0.37 Ω maximum on-resistance flatness
- 0.17 Ω maximum on-resistance match between channels
- Continuous current per channel
 - LFCSP package: 300 mA
 - TSSOP package: 190 mA
- Fully specified at +12 V, ±15 V, and ±5 V
- No V_L supply required
- 3 V logic-compatible inputs
- Rail-to-rail operation
- 16-lead TSSOP and 16-lead, 4 mm × 4 mm LFCSP

APPLICATIONS

- Automatic test equipment
- Data acquisition systems
- Battery-powered systems
- Sample-and-hold systems
- Audio signal routing
- Video signal routing
- Communication systems
- Relay replacement

GENERAL DESCRIPTION

The ADG1411/ADG1412/ADG1413 are monolithic complementary metal-oxide semiconductor (CMOS) devices containing four independently selectable switches designed on an *i*CMOS™ process. *i*CMOS (industrial CMOS) is a modular manufacturing process combining high voltage CMOS and bipolar technologies. It enables the development of a wide range of high performance analog ICs capable of 33 V operation in a footprint that no previous generation of high voltage parts has been able to achieve. Unlike analog ICs using conventional CMOS processes, *i*CMOS components can tolerate high supply voltages while providing increased performance, dramatically lower power consumption, and reduced package size.

The on-resistance profile is very flat over the full analog input range, ensuring excellent linearity and low distortion when switching audio signals.

*i*CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

The ADG1411/ADG1412/ADG1413 contain four independent single-pole/single-throw (SPST) switches. The ADG1411 and

FUNCTIONAL BLOCK DIAGRAM

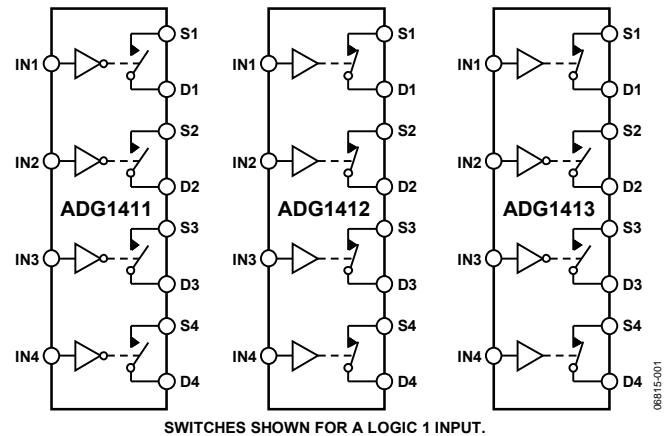


Figure 1.

ADG1412 differ only in that the digital control logic is inverted. The ADG1411 switches are turned on with Logic 0 on the appropriate control input, whereas the ADG1412 switches are turned on with Logic 1. The ADG1413 has two switches with digital control logic similar to that of the ADG1411; the logic is inverted on the other two switches. Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. In the off condition, signal levels up to the supplies are blocked.

The ADG1413 exhibits break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge injection for minimum transients when switching the digital inputs.

PRODUCT HIGHLIGHTS

- 2.5 Ω maximum on resistance over temperature.
- Minimum distortion
- Ultralow power dissipation: <0.03 μW.
- 16-lead TSSOP and 4 mm × 4 mm LFCSP packages.

Rev. PrF

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REVISION HISTORY

SPECIFICATIONS

15 V DUAL SUPPLY

$V_{DD} = 15\text{ V} \pm 10\%$, $V_{SS} = -15\text{ V} \pm 10\%$, GND = 0 V, unless otherwise noted.

Table 1.

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{DD} to V_{SS}	V	
On Resistance (R_{ON})	1.5			Ω typ	$V_S = \pm 10\text{ V}$, $I_S = -10\text{ mA}$; see Figure 23
	1.8	2.2	2.5	Ω max	$V_{DD} = +13.5\text{ V}$, $V_{SS} = -13.5\text{ V}$
On-Resistance Match Between Channels (ΔR_{ON})	0.1			Ω typ	$V_S = \pm 10\text{ V}$, $I_S = -10\text{ mA}$
	0.13	0.16	0.17	Ω max	
On-Resistance Flatness ($R_{FLAT(ON)}$)	0.28			Ω typ	$V_S = \pm 10\text{ V}$, $I_S = -10\text{ mA}$
	0.31	0.35	0.37	Ω max	
LEAKAGE CURRENTS					
Source Off Leakage, I_S (Off)	± 0.2			nA typ	$V_{DD} = +16.5\text{ V}$, $V_{SS} = -16.5\text{ V}$
	± 0.5	± 10	± 100	nA max	$V_S = \pm 10\text{ V}$, $V_D = \mp 10\text{ V}$; see Figure 24
Drain Off Leakage, I_D (Off)	± 0.2			nA typ	
	± 0.5	± 10	± 100	nA max	$V_S = \pm 10\text{ V}$, $V_D = \mp 10\text{ V}$; see Figure 24
Channel On Leakage, I_D , I_S (On)	± 0.2			nA typ	$V_S = V_D = \pm 10\text{ V}$; see Figure 25
	± 1	± 10	± 100	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.005			μA typ	$V_{IN} = V_{GND}$ or V_{DD}
			± 0.1	μA max	
Digital Input Capacitance, C_{IN}	3.5			pF typ	
DYNAMIC CHARACTERISTICS¹					
t_{ON}	100			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	150	170	190	ns max	$V_S = 10\text{ V}$; see Figure 30
t_{OFF}	90			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	120	140	160	ns max	$V_S = 10\text{ V}$; see Figure 30
Break-Before-Make Time Delay, t_D (ADG1413 only)	25		10	ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
				ns min	$V_{S1} = V_{S2} = 10\text{ V}$; Figure 31
Charge Injection	-20			pC typ	$V_S = 0\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32
Off Isolation	-80			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; see Figure 26
Channel-to-Channel Crosstalk	-100			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 27
Total Harmonic Distortion + Noise	0.011			% typ	$R_L = 110\ \Omega$, 15 V p-p, $f = 20\text{ Hz}$ to 20 kHz see Figure 29
-3 dB Bandwidth	206			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 28
Insertion Loss	-0.01			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 28
C_S (Off)	22			pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$
C_D (Off)	22			pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$
C_D , C_S (On)	104			pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$
POWER REQUIREMENTS					
I_{DD}	0.001			μA typ	$V_{DD} = +16.5\text{ V}$, $V_{SS} = -16.5\text{ V}$
			1	μA max	Digital inputs = 0 V or V_{DD}
I_{DD}	220			μA typ	Digital inputs = 5 V
			325	μA max	
I_{SS}	0.001			μA typ	Digital inputs = 0 V, 5 V, or V_{DD}
			1	μA max	
V_{DD}/V_{SS}			$\pm 4.5/\pm 16.5$	V min/max	GND = 0 V

¹ Guaranteed by design, not subject to production test.

12 V SINGLE SUPPLY

$V_{DD} = 12\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$, $GND = 0\text{ V}$, unless otherwise noted.

Table 2.

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance (R_{ON})	3			Ω typ	$V_S = 0\text{ V to }10\text{ V}$, $I_S = -10\text{ mA}$; see Figure 23
	3.5	4.3	4.7	Ω max	$V_{DD} = +10.8\text{ V}$, $V_{SS} = 0\text{ V}$
On-Resistance Match Between Channels (ΔR_{ON})	0.12			Ω typ	$V_S = 0\text{ V to }10\text{ V}$, $I_S = -10\text{ mA}$
	0.16	0.18	0.2	Ω max	
On-Resistance Flatness ($R_{FLAT(ON)}$)	0.85			Ω typ	$V_S = 0\text{ V to }10\text{ V}$, $I_S = -10\text{ mA}$
	1	1.13	1.16	Ω max	
LEAKAGE CURRENTS					
Source Off Leakage, I_S (Off)	± 0.2			nA typ	$V_{DD} = 13.2\text{ V}$, $V_{SS} = 0\text{ V}$
	± 0.5	± 10	± 100	nA max	$V_S = 1\text{ V}/10\text{ V}$, $V_D = 10\text{ V}/0\text{ V}$; see Figure 24
Drain Off Leakage, I_D (Off)	± 0.2			nA typ	$V_S = 1\text{ V}/10\text{ V}$, $V_D = 10\text{ V}/0\text{ V}$; see Figure 24
	± 0.5	± 10	± 100	nA max	
Channel On Leakage, I_D , I_S (On)	± 0.2			nA typ	$V_S = V_D = 1\text{ V or }10\text{ V}$; see Figure 25
	± 1.5	± 10	± 100	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.001			μA typ	$V_{IN} = V_{GND}$ or V_{DD}
			± 0.1	μA max	
Digital Input Capacitance, C_{IN}	3.5			pF typ	
DYNAMIC CHARACTERISTICS¹					
t_{ON}	170			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	250	295	330	ns max	$V_S = 8\text{ V}$; see Figure 30
t_{OFF}	75			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
	135	165	190	ns max	$V_S = 8\text{ V}$; see Figure 30
Break-Before-Make Time Delay, t_D (ADG1413 only)	100			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$
			40	ns min	$V_{S1} = V_{S2} = 8\text{ V}$; see Figure 31
Charge Injection	30			pC typ	$V_S = 6\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32
Off Isolation	-80			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; see Figure 26
Channel-to-Channel Crosstalk	-100			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 27
-3 dB Bandwidth	206			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 28
Insertion Loss	-0.03			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 28
C_S (Off)	38			pF typ	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$
C_D (Off)	40			pF typ	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$
C_D , C_S (On)	104			pF typ	$V_S = 6\text{ V}$, $f = 1\text{ MHz}$
POWER REQUIREMENTS					
I_{DD}	0.001			μA typ	$V_{DD} = 13.2\text{ V}$
			1	μA max	Digital inputs = 0 V or V_{DD}
I_{DD}	220			μA typ	Digital inputs = 5 V
			325	μA max	
V_{DD}			5/16.5	V min/max	$GND = 0\text{ V}$, $V_{SS} = 0\text{ V}$

¹ Guaranteed by design, not subject to production test.

5 V DUAL SUPPLY

$V_{DD} = 5\text{ V} \pm 10\%$, $V_{SS} = -5\text{ V} \pm 10\%$, $GND = 0\text{ V}$, unless otherwise noted.

Table 3.

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance (R_{ON})	3.5 4	4.8	5.3	Ω typ Ω max	$V_S = \pm 4.5\text{ V}$, $I_S = -10\text{ mA}$; see Figure 23 $V_{DD} = +4.5\text{ V}$, $V_{SS} = -4.5\text{ V}$
On-Resistance Match Between Channels (ΔR_{ON})	0.12			Ω typ	$V_S = \pm 4.5\text{ V}$, $I_S = -10\text{ mA}$
On-Resistance Flatness ($R_{FLAT(ON)}$)	0.16	0.18	0.2	Ω max	$V_S = \pm 4.5\text{ V}$; $I_S = -10\text{ mA}$
	0.88			Ω typ	
	1.1	1.2	1.3	Ω max	
LEAKAGE CURRENTS					
Source Off Leakage, I_S (Off)	± 0.01			nA typ	$V_{DD} = +5.5\text{ V}$, $V_{SS} = -5.5\text{ V}$ $V_S = \pm 4.5\text{ V}$, $V_D = \mp 4.5\text{ V}$; see Figure 24
Drain Off Leakage, I_D (Off)	± 0.5	± 10	± 100	nA max	$V_S = \pm 4.5\text{ V}$, $V_D = \mp 4.5\text{ V}$; see Figure 24
	± 0.01			nA typ	
Channel On Leakage, I_D , I_S (On)	± 0.5	± 10	± 100	nA max	$V_S = V_D = \pm 4.5\text{ V}$; see Figure 25
	± 0.07			nA typ	
	± 1	± 10	± 100	nA max	
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.0	V min	$V_{IN} = V_{GND}$ or V_{DD}
Input Low Voltage, V_{INL}			0.8	V max	
Input Current, I_{INL} or I_{INH}	0.001		± 0.1	μA typ μA max	
Digital Input Capacitance, C_{IN}	3.5			pF typ	
DYNAMIC CHARACTERISTICS¹					
t_{ON}	275			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 3\text{ V}$; see Figure 30
	400	465	510	ns max	
t_{OFF}	175			ns typ	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_S = 3\text{ V}$; see Figure 30
	290	320	380	ns max	
Break-Before-Make Time Delay, t_D (ADG1413 only)	100		50	ns typ ns min	$R_L = 300\ \Omega$, $C_L = 35\text{ pF}$ $V_{S1} = V_{S2} = 3\text{ V}$; see Figure 31
Charge Injection	30			pC typ	$V_S = 0\text{ V}$, $R_S = 0\ \Omega$, $C_L = 1\text{ nF}$; see Figure 32
Off Isolation	-80			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 100\text{ kHz}$; see Figure 26
Channel-to-Channel Crosstalk	-100			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 27
Total Harmonic Distortion + Noise	0.03			% typ	$R_L = 110\ \Omega$, 5 V p-p, $f = 20\text{ Hz}$ to 20 kHz; see Figure 29
-3 dB Bandwidth	145			MHz typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$; see Figure 28
Insertion Loss	-0.12			dB typ	$R_L = 50\ \Omega$, $C_L = 5\text{ pF}$, $f = 1\text{ MHz}$; see Figure 28
C_S (Off)	32			pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$
C_D (Off)	33			pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$
C_D , C_S (On)	116			pF typ	$V_S = 0\text{ V}$, $f = 1\text{ MHz}$
POWER REQUIREMENTS					
I_{DD}	0.001			μA typ	$V_{DD} = 5.5\text{ V}$, $V_{SS} = -5.5\text{ V}$ Digital inputs = 0 V or V_{DD}
I_{SS}	0.001		1.0	μA max	Digital inputs = 5 V
			1.0	μA typ	
V_{DD}/V_{SS}			$\pm 4.5/\pm 16.5$	V min/max	$GND = 0\text{ V}$

¹ Guaranteed by design, not subject to production test.

ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 4.

Parameter	Rating
V_{DD} to V_{SS}	35 V
V_{DD} to GND	-0.3 V to +25 V
V_{SS} to GND	+0.3 V to -25 V
Analog Inputs ¹	$V_{SS} - 0.3\text{ V}$ to $V_{DD} + 0.3\text{ V}$
Digital Inputs ¹	GND - 0.3 V to $V_{DD} + 0.3\text{ V}$ or 30 mA, whichever occurs first
Peak Current, S or D	600 mA (pulsed at 1 ms, 10% duty cycle maximum)
Continuous Current per Channel, S or D	
16-Lead TSSOP	190 mA
16-Lead LFCSP	300 mA
Operating Temperature Range	
Automotive (Y Version)	-40°C to +125°C
Storage Temperature Range	-65°C to +150°C
Junction Temperature	150°C
16-Lead TSSOP, θ_{JA} Thermal Impedance (4-layer board)	112°C/W
16-Lead LFCSP, θ_{JA} Thermal Impedance	30.4°C/W
Reflow Soldering Peak Temperature, Pb free	260(+0/-5)°C

¹ Overvoltages at IN, S, and D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating may be applied at any one time.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

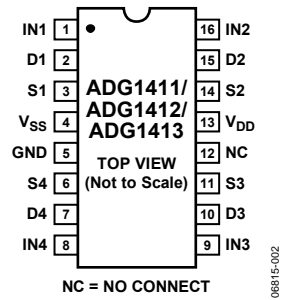


Figure 2. TSSOP Pin Configuration

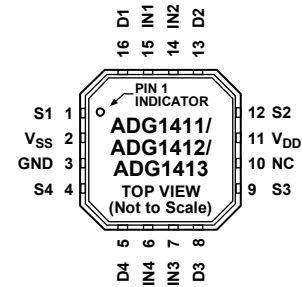


Figure 3. LFCSP Pin Configuration

Table 5. Pin Function Descriptions

Pin No.		Mnemonic	Description
TSSOP	LFCSP		
1	15	IN1	Logic Control Input.
2	16	D1	Drain Terminal. Can be an input or output.
3	1	S1	Source Terminal. Can be an input or output.
4	2	V _{SS}	Most Negative Power Supply Potential.
5	3	GND	Ground (0 V) Reference.
6	4	S4	Source Terminal. Can be an input or output.
7	5	D4	Drain Terminal. Can be an input or output.
8	6	IN4	Logic Control Input.
9	7	IN3	Logic Control Input.
10	8	D3	Drain Terminal. Can be an input or output.
11	9	S3	Source Terminal. Can be an input or output.
12	10	NC	No Connection.
13	11	V _{DD}	Most Positive Power Supply Potential.
14	12	S2	Source Terminal. Can be an input or output.
15	13	D2	Drain Terminal. Can be an input or output.
16	14	IN2	Logic Control Input.

Table 6. ADG1411/ADG1412 Truth Table

ADG1411 IN _x	ADG1412 IN _x	Switch Condition
0	1	On
1	0	Off

Table 7. ADG1413 Truth Table

ADG1413 IN _x	S1, S4	S2, S3
0	Off	On
1	On	Off

TERMINOLOGY

I_{DD}

The positive supply current.

I_{SS}

The negative supply current.

V_D (V_S)

The analog voltage on Terminal D and Terminal S.

R_{ON}

The ohmic resistance between Terminal D and Terminal S.

$R_{FLAT(ON)}$

Flatness is defined as the difference between the maximum and minimum value of on resistance measured over the specified analog signal range.

I_S (Off)

The source leakage current with the switch off.

I_D (Off)

The drain leakage current with the switch off.

I_D, I_S (On)

The channel leakage current with the switch on.

V_{INL}

The maximum input voltage for Logic 0.

V_{INH}

The minimum input voltage for Logic 1.

I_{INL} (I_{INH})

The input current of the digital input.

C_S (Off)

The off switch source capacitance, which is measured with reference to ground.

C_D (Off)

The off switch drain capacitance, which is measured with reference to ground.

C_D, C_S (On)

The on switch capacitance, which is measured with reference to ground.

C_{IN}

The digital input capacitance.

t_{ON}

The delay between applying the digital control input and the output switching on. See Figure 30.

t_{OFF}

The delay between applying the digital control input and the output switching off.

Charge Injection

A measure of the glitch impulse transferred from the digital input to the analog output during switching.

Off Isolation

A measure of unwanted signal coupling through an off switch.

Crosstalk

A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.

Bandwidth

The frequency at which the output is attenuated by 3 dB.

On Response

The frequency response of the on switch.

Insertion Loss

The loss due to the on resistance of the switch.

THD + N

The ratio of the harmonic amplitude plus noise of the signal to the fundamental.

ACPSRR (AC Power Supply Rejection Ratio)

Measures the ability of a part to avoid coupling noise and spurious signals that appear on the supply voltage pin to the output of the switch. The dc voltage on the device is modulated by a sine wave of 0.62 V p-p. The ratio of the amplitude of signal on the output to the amplitude of the modulation is the ACPSRR.

TYPICAL PERFORMANCE CHARACTERISTICS

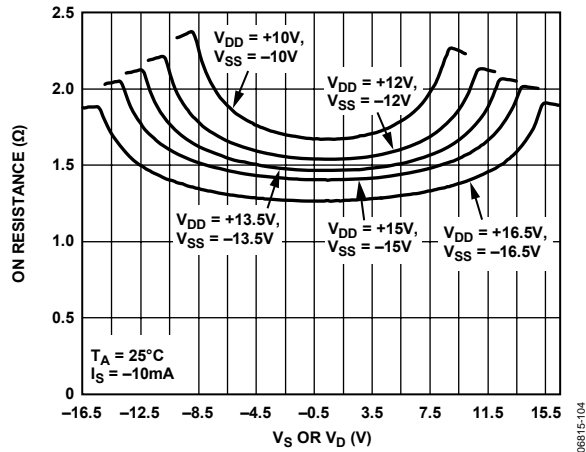


Figure 4. On Resistance as a Function of V_D (V_S), Dual Supply

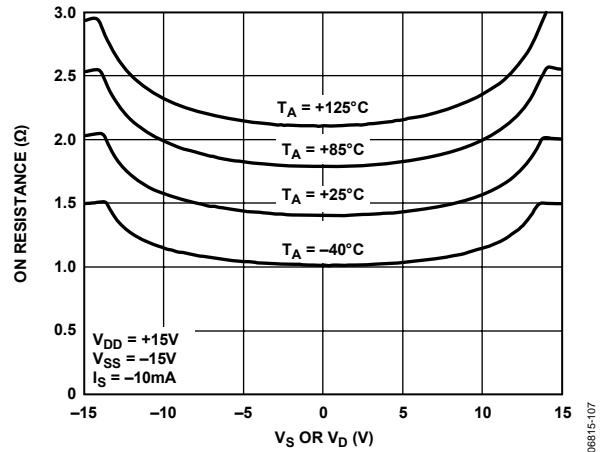


Figure 7. On Resistance as a Function of V_D (V_S) for Different Temperatures, 15 V Dual Supply

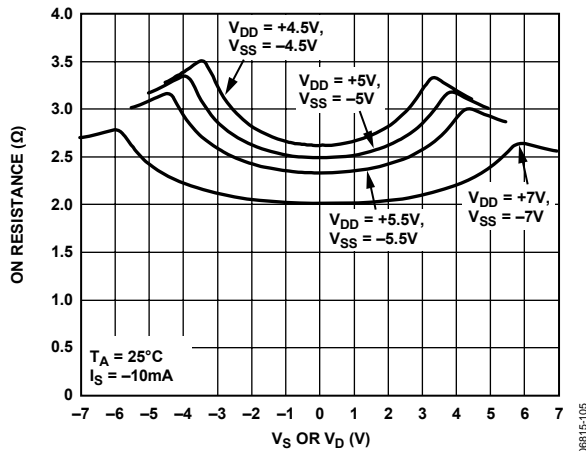


Figure 5. On Resistance as a Function of V_D (V_S), Dual Supply

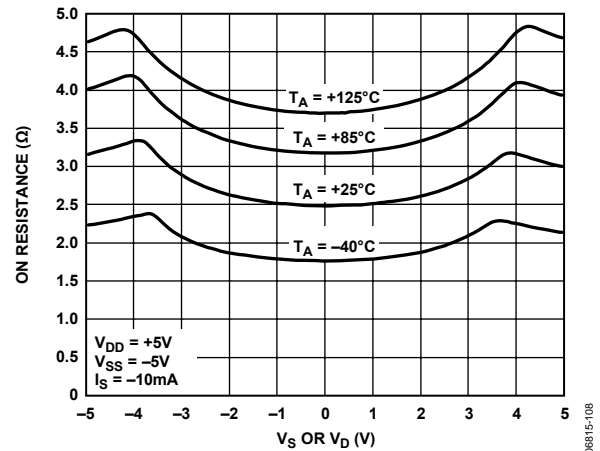


Figure 8. On Resistance as a Function of V_D (V_S) for Different Temperatures, 5 V Dual Supply

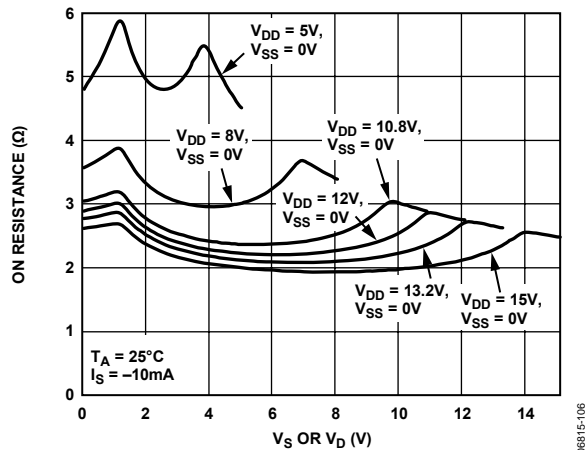


Figure 6. On Resistance as a Function of V_D (V_S), Single Supply

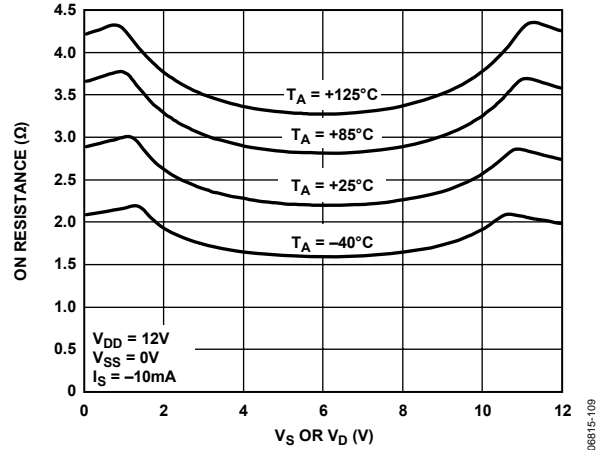


Figure 9. On Resistance as a Function of V_D (V_S) for Different Temperatures, Single Supply

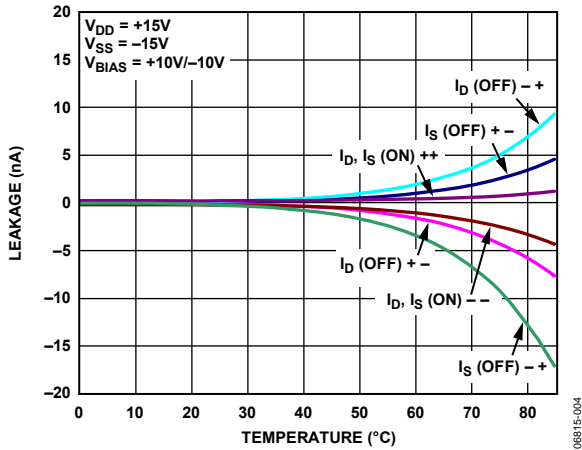


Figure 10. Leakage Currents as a Function of Temperature, 15 V Dual Supply

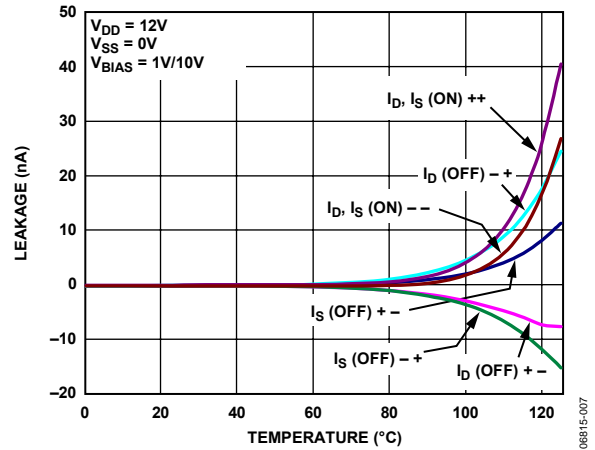


Figure 13. Leakage Currents as a Function of Temperature, Single Supply

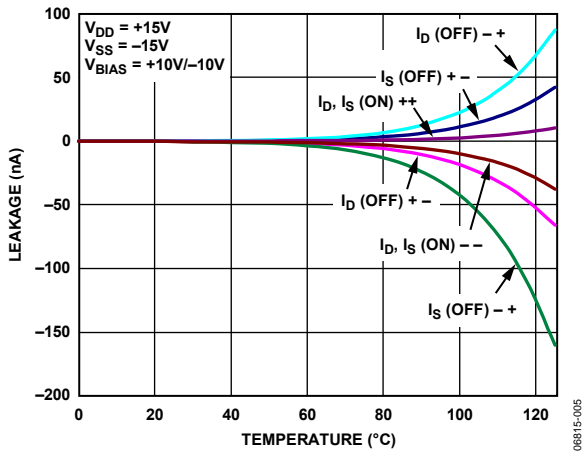


Figure 11. Leakage Currents as a Function of Temperature, 15 V Dual Supply

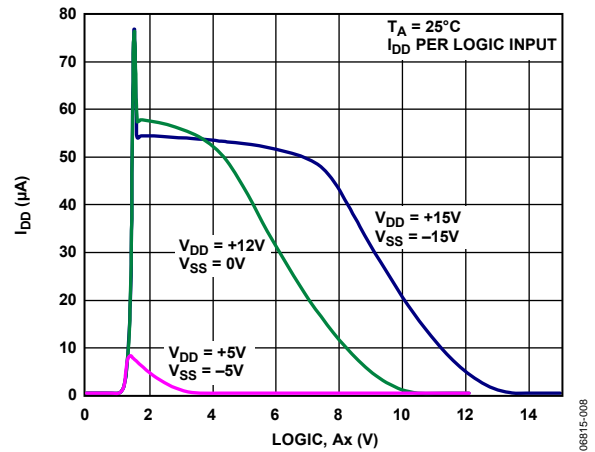


Figure 14. I_{DD} vs. Logic Level

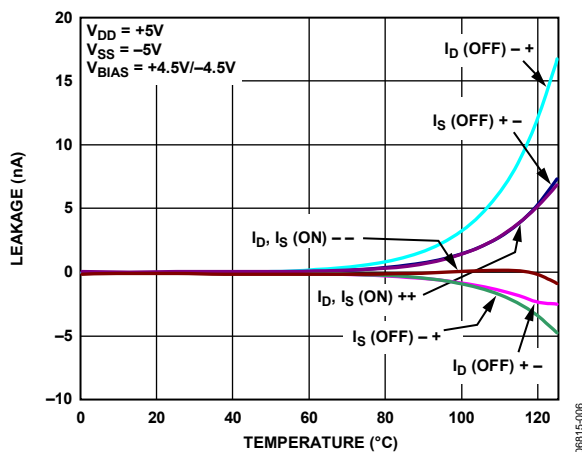


Figure 12. Leakage Currents as a Function of Temperature, Dual Supply

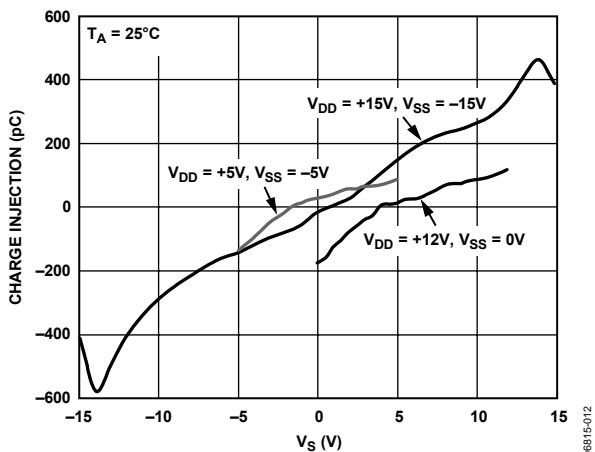


Figure 15. Charge Injection vs. Source Voltage

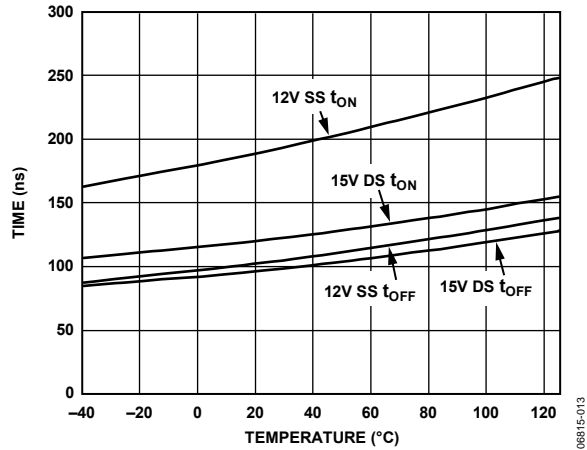


Figure 16. t_{ON}/t_{OFF} Times vs. Temperature

06815-013

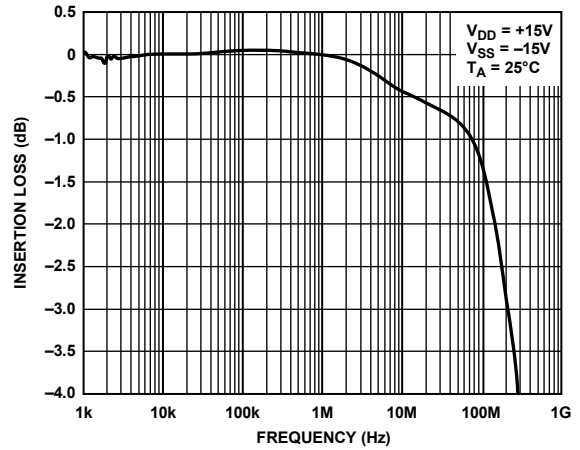


Figure 19. On Response vs. Frequency

06815-016

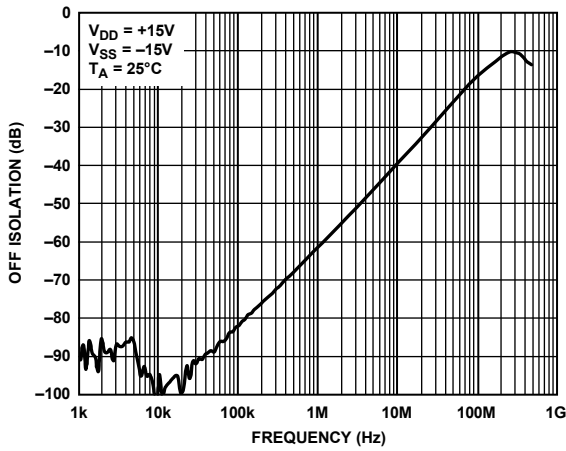


Figure 17. Off Isolation vs. Frequency

06815-014

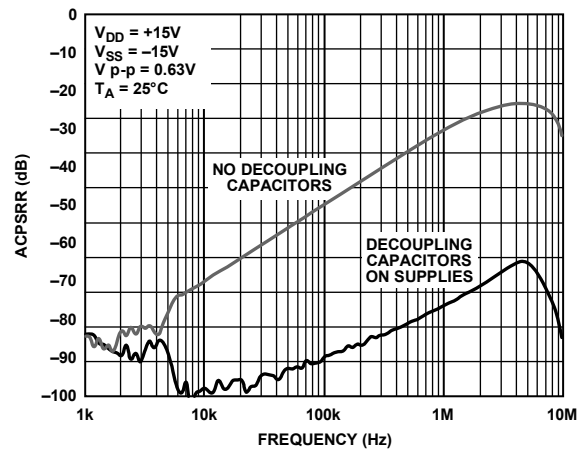


Figure 20. ACPSRR vs. Frequency

06815-017

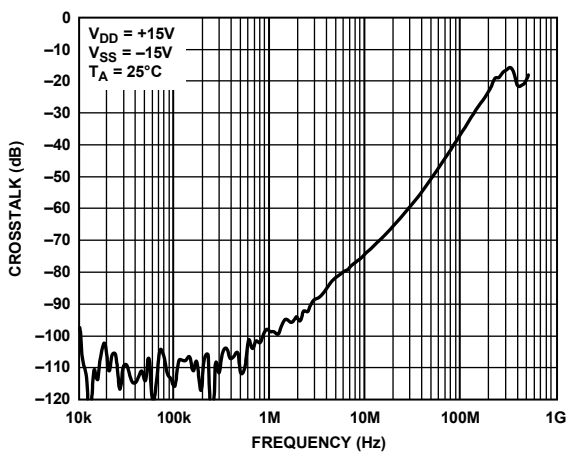


Figure 18. Crosstalk vs. Frequency

06815-015

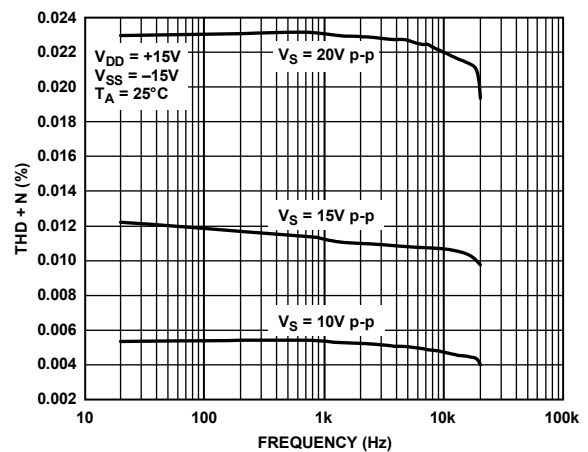


Figure 21. THD + N vs. Frequency, 15 V Dual Supply

06815-017

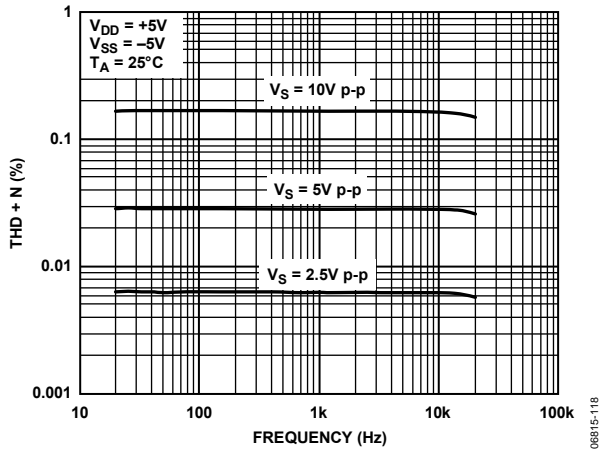


Figure 22. THD + N vs. Frequency, 5 V Dual Supply

06815-118

TEST CIRCUITS

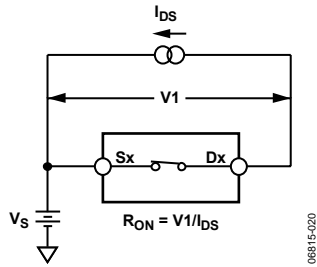


Figure 23. On Resistance

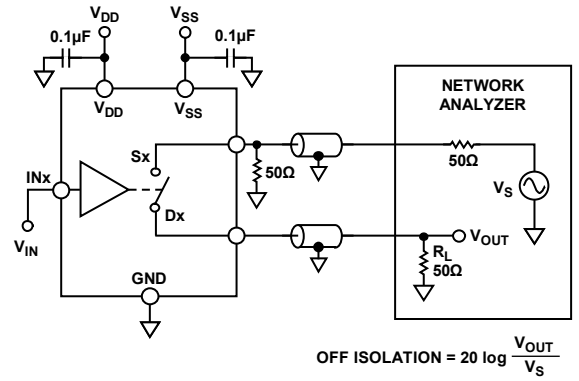


Figure 26. Off Isolation

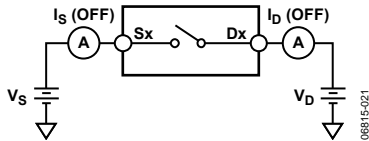


Figure 24. Off Leakage

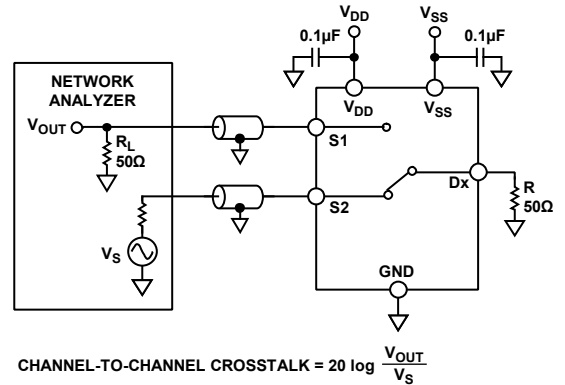


Figure 27. Channel-to-Channel Crosstalk

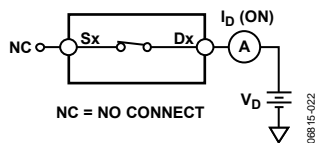


Figure 25. On Leakage

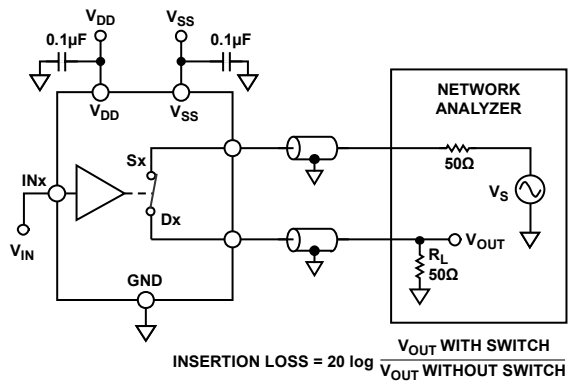


Figure 28. Bandwidth

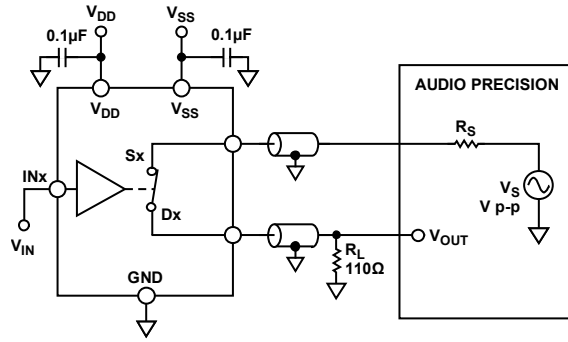


Figure 29. THD + Noise

06815-029

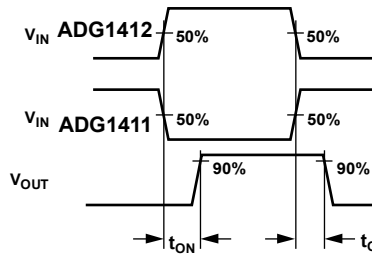
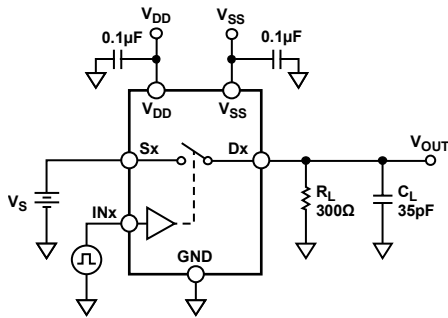


Figure 30. Switching Times

06815-023

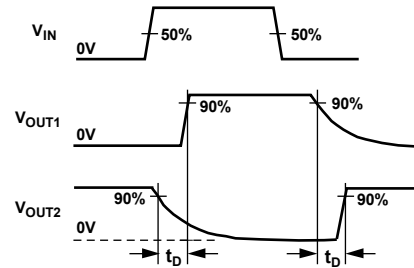
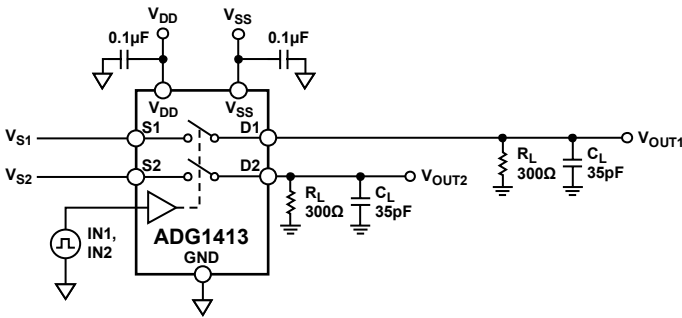


Figure 31. Break-Before-Make Time Delay

06815-024

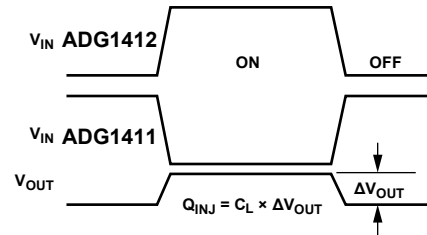
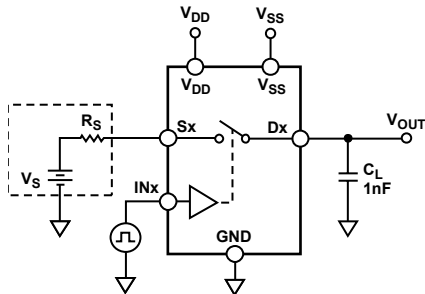
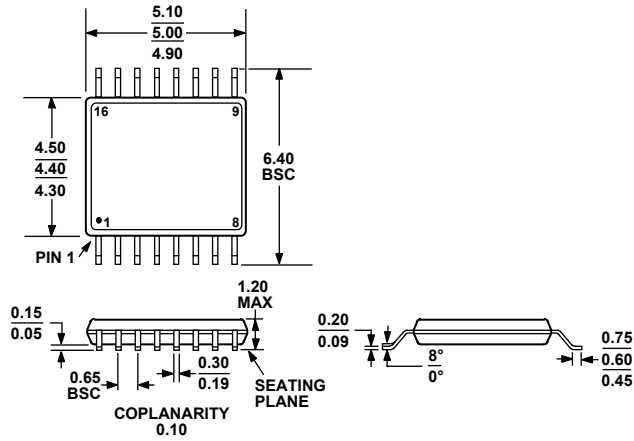


Figure 32. Charge Injection

06815-025

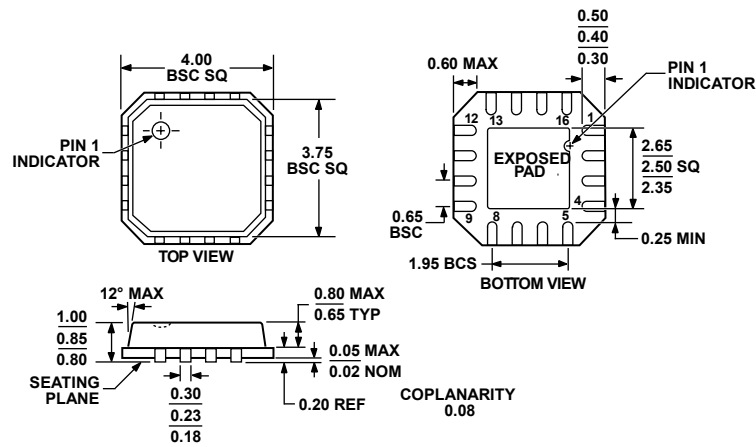
OUTLINE DIMENSIONS



COMPLIANT TO JEDEC STANDARDS MO-153-AB

Figure 33. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16)

Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-220-VGGC.

Figure 34. 16-Lead Lead Frame Chip Scale Package [LFCSQ_VQ] 4 mm x 4 mm Body, Very Thin Quad (CP-16-13)

Dimensions shown in millimeters

051005-A

ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG1411YRUZ ¹	–40°C to +125°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG1411YRUZ-REEL ¹	–40°C to +125°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG1411YCPZ-REEL ¹	–40°C to +125°C	16-Lead Lead Frame Chip Scale Package (LFCSP_VQ)	CP-16-13
ADG1411YCPZ-REEL ¹	–40°C to +125°C	16-Lead Lead Frame Chip Scale Package (LFCSP_VQ)	CP-16-13
ADG1412YRUZ ¹	–40°C to +125°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG1412YRUZ-REEL ¹	–40°C to +125°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG1412YCPZ-REEL ¹	–40°C to +125°C	16-Lead Lead Frame Chip Scale Package (LFCSP_VQ)	CP-16-13
ADG1412YCPZ-REEL ¹	–40°C to +125°C	16-Lead Lead Frame Chip Scale Package (LFCSP_VQ)	CP-16-13
ADG1413YRUZ ¹	–40°C to +125°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG1413YRUZ-REEL ¹	–40°C to +125°C	16-Lead Thin Shrink Small Outline Package (TSSOP)	RU-16
ADG1413YCPZ-REEL ¹	–40°C to +125°C	16-Lead Lead Frame Chip Scale Package (LFCSP_VQ)	CP-16-13
ADG1413YCPZ-REEL ¹	–40°C to +125°C	16-Lead Lead Frame Chip Scale Package (LFCSP_VQ)	CP-16-13

¹ Z = RoHS Compliant Part.